

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

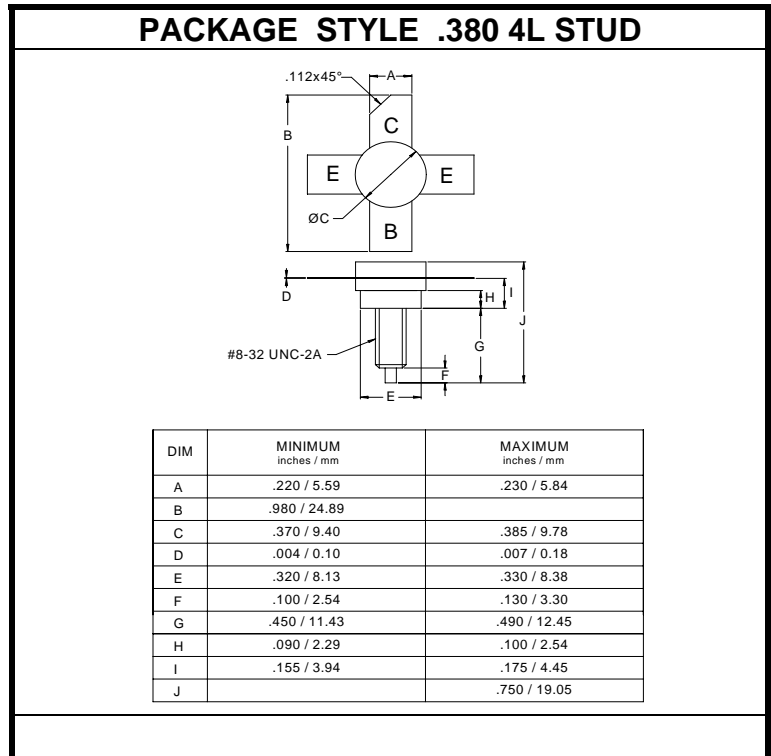
The **ASI BLW31** is an NPN power transistor, designed 108-175 MHz applications. The device utilizes diffused emitter resistors to achieve good VSWR capability

FEATURES:

- Common Emitter-Class-C
- $P_G = 10$ dB at 30 W/150 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CB0}	36 V
V_{CEO}	18 V
V_{EBO}	4.0 V
P_{DISS}	40 W @ $T_C = 25$ °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	4.4 °C/W



CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200$ mA	35			V
BV_{CES}	$I_C = 200$ mA	65			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			2.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 200$ mA	35		---	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			250	pF
P_G η_C	$V_{CC} = 28$ V $P_{OUT} = 25$ W $f = 175$ MHz	8.5	60		dB %